

# Eduardo Alves

## List of Publications by Citations

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769  
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794  
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12,700  
ext. citations

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avg, IF

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L-index

#	Paper	IF	Citations
769	Effect of post-annealing on the properties of copper oxide thin films obtained from the oxidation of evaporated metallic copper. <i>Applied Surface Science</i> , <b>2008</b> , 254, 3949-3954	6.7	187
768	Strain and composition distributions in wurtzite InGa <sub>N</sub> /Ga <sub>N</sub> layers extracted from x-ray reciprocal space mapping. <i>Applied Physics Letters</i> , <b>2002</b> , 80, 3913-3915	3.4	187
767	Characterisation of Ti <sub>1-x</sub> Si <sub>x</sub> Ny nanocomposite films. <i>Surface and Coatings Technology</i> , <b>2000</b> , 133-134, 307-313	4.4	177
766	Compositional pulling effects in In <sub>x</sub> Ga <sub>1-x</sub> N/Ga <sub>N</sub> layers: A combined depth-resolved cathodoluminescence and Rutherford backscattering/channeling study. <i>Physical Review B</i> , <b>2001</b> , 64,	3.3	159
765	Structural, optical and mechanical properties of coloured Ti <sub>N</sub> O <sub>y</sub> thin films. <i>Thin Solid Films</i> , <b>2004</b> , 447-448, 449-454	2.2	157
764	Overview of the JET results in support to ITER. <i>Nuclear Fusion</i> , <b>2017</b> , 57, 102001	3.3	125
763	Anomalous ion channeling in AlIn <sub>N</sub> /Ga <sub>N</sub> bilayers: determination of the strain state. <i>Physical Review Letters</i> , <b>2006</b> , 97, 085501	7.4	119
762	Influence of nitrogen content on the structural, mechanical and electrical properties of TiN thin films. <i>Surface and Coatings Technology</i> , <b>2005</b> , 191, 317-323	4.4	118
761	Microstructure and mechanical properties of nanocomposite (Ti,Si,Al) <sub>N</sub> coatings. <i>Thin Solid Films</i> , <b>2001</b> , 398-399, 391-396	2.2	112
760	Metal-organic vapor phase epitaxy and properties of AlIn <sub>N</sub> in the whole compositional range. <i>Applied Physics Letters</i> , <b>2007</b> , 90, 022105	3.4	111
759	Hard nanocomposite Ti <sub>1-x</sub> Si <sub>x</sub> N coatings prepared by DC reactive magnetron sputtering. <i>Surface and Coatings Technology</i> , <b>2000</b> , 133-134, 234-239	4.4	110
758	Materials design data for reduced activation martensitic steel type EUROFER. <i>Journal of Nuclear Materials</i> , <b>2004</b> , 329-333, 257-262	3.3	106
757	Compositional dependence of the strain-free optical band gap in In <sub>x</sub> Ga <sub>1-x</sub> N layers. <i>Applied Physics Letters</i> , <b>2001</b> , 78, 2137-2139	3.4	93
756	Structural and optical properties of InGa <sub>N</sub> /Ga <sub>N</sub> layers close to the critical layer thickness. <i>Applied Physics Letters</i> , <b>2002</b> , 81, 1207-1209	3.4	92
755	Damage formation and annealing at low temperatures in ion implanted ZnO. <i>Applied Physics Letters</i> , <b>2005</b> , 87, 191904	3.4	90
754	Photoluminescence and lattice location of Eu and Pr implanted Ga <sub>N</sub> samples. <i>Physica B: Condensed Matter</i> , <b>2001</b> , 308-310, 22-25	2.8	87
753	Direct evidence for As as a Zn-site impurity in ZnO. <i>Physical Review Letters</i> , <b>2005</b> , 95, 215503	7.4	82

752	Selectively excited photoluminescence from Eu-implanted GaN. <i>Applied Physics Letters</i> , <b>2005</b> , 87, 112107	3.4	80
751	Structural, electrical, optical, and mechanical characterizations of decorative ZrOxNy thin films. <i>Journal of Applied Physics</i> , <b>2005</b> , 98, 023715	2.5	79
750	Photoluminescence studies in ZnO samples. <i>Physica B: Condensed Matter</i> , <b>2001</b> , 308-310, 985-988	2.8	78
749	Effects of ion bombardment on properties of d.c. sputtered superhard (Ti, Si, Al)N nanocomposite coatings. <i>Surface and Coatings Technology</i> , <b>2002</b> , 151-152, 515-520	4.4	74
748	Synthesis, surface modification and optical properties of Tb <sup>3+</sup> -doped ZnO nanocrystals. <i>Nanotechnology</i> , <b>2006</b> , 17, 834-839	3.4	72
747	Preparation of magnetron sputtered TiNxOy thin films. <i>Surface and Coatings Technology</i> , <b>2003</b> , 174-175, 197-203	4.4	72
746	Tuning of the surface plasmon resonance in TiO <sub>2</sub> /Au thin films grown by magnetron sputtering: The effect of thermal annealing. <i>Journal of Applied Physics</i> , <b>2011</b> , 109, 074310	2.5	68
745	Three-step amorphisation process in ion-implanted GaN at 15 K. <i>Nuclear Instruments &amp; Methods in Physics Research B</i> , <b>2003</b> , 206, 1028-1032	1.2	66
744	Material migration patterns and overview of first surface analysis of the JET ITER-like wall. <i>Physica Scripta</i> , <b>2014</b> , T159, 014010	2.6	65
743	Characterization of TiAlSiN/TiAlSiON/SiO <sub>2</sub> optical stack designed by modelling calculations for solar selective applications. <i>Solar Energy Materials and Solar Cells</i> , <b>2012</b> , 105, 202-207	6.4	64
742	High-temperature annealing and optical activation of Eu-implanted GaN. <i>Applied Physics Letters</i> , <b>2004</b> , 85, 2712-2714	3.4	64
741	Lattice site location and optical activity of Er implanted ZnO. <i>Nuclear Instruments &amp; Methods in Physics Research B</i> , <b>2003</b> , 206, 1047-1051	1.2	64
740	Identification of the prime optical center in GaN:Eu <sup>3+</sup> . <i>Physical Review B</i> , <b>2010</b> , 81,	3.3	61
739	Property change in ZrNxOy thin films: effect of the oxygen fraction and bias voltage. <i>Thin Solid Films</i> , <b>2004</b> , 469-470, 11-17	2.2	61
738	Micron-scale analysis of SiC/SiCf composites using the new Lisbon nuclear microprobe. <i>Nuclear Instruments &amp; Methods in Physics Research B</i> , <b>2000</b> , 161-163, 334-338	1.2	61
737	Electrical, structural and optical characterization of copper oxide thin films as a function of post annealing temperature. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2009</b> , 206, 2143-2148	1.6	60
736	Role of Nanoscale Strain Inhomogeneity on the Light Emission from InGaN Epilayers. <i>Advanced Functional Materials</i> , <b>2007</b> , 17, 37-42	15.6	59
735	Radiation damage in ZnO ion implanted at 15K. <i>Nuclear Instruments &amp; Methods in Physics Research B</i> , <b>2009</b> , 267, 2708-2711	1.2	58

734	Efficient dipole-dipole coupling of Mott-Wannier and Frenkel excitons in (Ga,In)N quantum well/polyfluorene semiconductor heterostructures. <i>Physical Review B</i> , <b>2007</b> , 76,	3.3	57
733	Solar selective absorbers based on Al <sub>2</sub> O <sub>3</sub> :W cermet and AlSiN/AlSiON layers. <i>Solar Energy Materials and Solar Cells</i> , <b>2015</b> , 137, 93-100	6.4	56
732	Influence of the chemical and electronic structure on the electrical behavior of zirconium oxynitride films. <i>Journal of Applied Physics</i> , <b>2008</b> , 103, 104907	2.5	56
731	Optical energies of AlInN epilayers. <i>Journal of Applied Physics</i> , <b>2008</b> , 103, 073510	2.5	56
730	Dielectric function of nanocrystalline silicon with few nanometers (. <i>Applied Physics Letters</i> , <b>2003</b> , 82, 2993-2995	3.4	56
729	Photoluminescence and damage recovery studies in Fe-implanted ZnO single crystals. <i>Journal of Applied Physics</i> , <b>2003</b> , 93, 8995-9000	2.5	56
728	Overview of the JET preparation for deuterium-tritium operation with the ITER like-wall. <i>Nuclear Fusion</i> , <b>2019</b> , 59, 112021	3.3	55
727	Transmission electron microscopy investigation of the structural damage formed in GaN by medium range energy rare earth ion implantation. <i>Journal of Applied Physics</i> , <b>2006</b> , 100, 073520	2.5	55
726	Implantation damage formation in a-, c- and m-plane GaN. <i>Acta Materialia</i> , <b>2017</b> , 123, 177-187	8.4	54
725	An overview of the comprehensive First Mirror Test in JET with ITER-like wall. <i>Physica Scripta</i> , <b>2014</b> , T159, 014011	2.6	53
724	Near-band-edge slow luminescence in nominally undoped bulk ZnO. <i>Journal of Applied Physics</i> , <b>2005</b> , 98, 013502	2.5	53
723	Raman study of the A <sub>1</sub> (LO) phonon in relaxed and pseudomorphic InGaN epilayers. <i>Applied Physics Letters</i> , <b>2003</b> , 83, 4761-4763	3.4	53
722	Identification of donor-related impurities in ZnO using photoluminescence and radiotracer techniques. <i>Physical Review B</i> , <b>2006</b> , 73,	3.3	52
721	Implantation site of rare earths in single-crystalline ZnO. <i>Applied Physics Letters</i> , <b>2003</b> , 82, 1173-1175	3.4	51
720	Application of RZ-scan technique for investigation of nonlinear refraction of sapphire doped with Ag, Cu, and Au nanoparticles. <i>Optics Communications</i> , <b>2005</b> , 253, 205-213	2	51
719	Plasma-wall interaction studies within the EUROfusion consortium: progress on plasma-facing components development and qualification. <i>Nuclear Fusion</i> , <b>2017</b> , 57, 116041	3.3	50
718	Lattice location and thermal stability of implanted Fe in ZnO. <i>Applied Physics Letters</i> , <b>2004</b> , 85, 4899-4901	3.4	49
717	Optical studies of ZnO nanocrystals doped with Eu <sup>3+</sup> ions. <i>Applied Physics A: Materials Science and Processing</i> , <b>2007</b> , 88, 129-133	2.6	48

716	Corrosion resistance of ZrN <sub>x</sub> O <sub>y</sub> thin films obtained by rf reactive magnetron sputtering. <i>Thin Solid Films</i> , <b>2004</b> , 469-470, 274-281	2.2	48
715	Interpretation of double x-ray diffraction peaks from InGaN layers. <i>Applied Physics Letters</i> , <b>2001</b> , 79, 1433-1434	3.4	48
714	Radiation damage formation and annealing in GaN and ZnO <b>2011</b> ,		47
713	High temperature annealing of rare earth implanted GaN films: Structural and optical properties. <i>Optical Materials</i> , <b>2006</b> , 28, 750-758	3.3	47
712	High Orbital Angular Momentum Harmonic Generation. <i>Physical Review Letters</i> , <b>2016</b> , 117, 265001	7.4	46
711	Microstructure of (Ti,Si,Al)N nanocomposite coatings. <i>Surface and Coatings Technology</i> , <b>2004</b> , 177-178, 369-375	4.4	45
710	Long-term fuel retention in JET ITER-like wall. <i>Physica Scripta</i> , <b>2016</b> , T167, 014075	2.6	44
709	The influence of annealing treatments on the properties of Ag:TiO <sub>2</sub> nanocomposite films prepared by magnetron sputtering. <i>Applied Surface Science</i> , <b>2012</b> , 258, 4028-4034	6.7	44
708	Relaxation of compressively strained AlInN on GaN. <i>Journal of Crystal Growth</i> , <b>2008</b> , 310, 4058-4064	1.6	44
707	Transparent thin film transistors based on indium oxide semiconductor. <i>Journal of Non-Crystalline Solids</i> , <b>2006</b> , 352, 2311-2314	3.9	44
706	Fuel retention in JET ITER-Like Wall from post-mortem analysis. <i>Journal of Nuclear Materials</i> , <b>2015</b> , 463, 961-965	3.3	43
705	Structural and optical characterization of Eu-implanted GaN. <i>Journal Physics D: Applied Physics</i> , <b>2009</b> , 42, 165103	3	43
704	Global erosion and deposition patterns in JET with the ITER-like wall. <i>Journal of Nuclear Materials</i> , <b>2015</b> , 463, 157-161	3.3	42
703	Structural evolution in ZrN <sub>x</sub> O <sub>y</sub> thin films as a function of temperature. <i>Surface and Coatings Technology</i> , <b>2006</b> , 200, 2917-2922	4.4	42
702	High Mobility a-IGO Films Produced at Room Temperature and Their Application in TFTs. <i>Electrochemical and Solid-State Letters</i> , <b>2010</b> , 13, H20		41
701	PVD-Grown photocatalytic TiO <sub>2</sub> thin films on PVDF substrates for sensors and actuators applications. <i>Thin Solid Films</i> , <b>2008</b> , 517, 1161-1166	2.2	41
700	Mechanical characterization of reactively magnetron-sputtered TiN films. <i>Surface and Coatings Technology</i> , <b>2003</b> , 174-175, 375-382	4.4	41
699	Elastic properties of (Ti,Al,Si)N nanocomposite films. <i>Surface and Coatings Technology</i> , <b>2001</b> , 142-144, 110-116	4.4	41

698	Optimization of nanocomposite Au/TiO <sub>2</sub> thin films towards LSPR optical-sensing. <i>Applied Surface Science</i> , <b>2018</b> , 438, 74-83	6.7	40
697	Lattice location and optical activation of rare earth implanted GaN. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2003</b> , 105, 132-140	3.1	40
696	Free electron behavior in InN: On the role of dislocations and surface electron accumulation. <i>Applied Physics Letters</i> , <b>2009</b> , 94, 022109	3.4	38
695	Identifying the influence of the intrinsic defects in Gd-doped ZnO thin-films. <i>Journal of Applied Physics</i> , <b>2016</b> , 119, 065301	2.5	38
694	Cathodoluminescence of rare earth implanted Ga <sub>2</sub> O <sub>3</sub> and GeO <sub>2</sub> nanostructures. <i>Nanotechnology</i> , <b>2011</b> , 22, 285706	3.4	37
693	Optically active centers in Eu implanted, Eu in situ doped GaN, and Eu doped GaN quantum dots. <i>Journal of Applied Physics</i> , <b>2009</b> , 105, 043104	2.5	37
692	Hydrogenated silicon carbon nitride films obtained by HWCVD, PA-HWCVD and PECVD techniques. <i>Journal of Non-Crystalline Solids</i> , <b>2006</b> , 352, 1361-1366	3.9	37
691	Lattice location and stability of implanted Cu in ZnO. <i>Physical Review B</i> , <b>2004</b> , 69,	3.3	37
690	Room-temperature growth of crystalline indium tin oxide films on glass using low-energy oxygen-ion-beam assisted deposition. <i>Journal of Applied Physics</i> , <b>2003</b> , 93, 2262-2266	2.5	37
689	Overview of the JET ITER-like wall divertor. <i>Nuclear Materials and Energy</i> , <b>2017</b> , 12, 499-505	2.1	36
688	Optical doping and damage formation in AlN by Eu implantation. <i>Journal of Applied Physics</i> , <b>2010</b> , 107, 023525	2.5	36
687	Ion beam studies of TiN <sub>x</sub> O <sub>y</sub> thin films deposited by reactive magnetron sputtering. <i>Surface and Coatings Technology</i> , <b>2004</b> , 180-181, 372-376	4.4	36
686	Optical and structural analysis of solar selective absorbing coatings based on AlSiO <sub>x</sub> :W cermet. <i>Solar Energy</i> , <b>2017</b> , 150, 335-344	6.8	35
685	Overview of fuel inventory in JET with the ITER-like wall. <i>Nuclear Fusion</i> , <b>2017</b> , 57, 086045	3.3	35
684	Functional and optical properties of Au:TiO <sub>2</sub> nanocomposite films: The influence of thermal annealing. <i>Applied Surface Science</i> , <b>2010</b> , 256, 6536-6542	6.7	35
683	Structural and corrosion behaviour of stoichiometric and substoichiometric TiN thin films. <i>Surface and Coatings Technology</i> , <b>2004</b> , 180-181, 158-163	4.4	35
682	Structural and luminescence properties of Eu and Er implanted Bi <sub>2</sub> O <sub>3</sub> nanowires for optoelectronic applications. <i>Journal of Materials Chemistry C</i> , <b>2013</b> , 1, 7920	7.1	34
681	Mechanisms of damage formation in Eu-implanted GaN probed by X-ray diffraction. <i>Europhysics Letters</i> , <b>2011</b> , 96, 46002	1.6	34

680	Enhancement in the photocatalytic nature of nitrogen-doped PVD-grown titanium dioxide thin films. <i>Journal of Applied Physics</i> , <b>2009</b> , 106, 113535	2.5	33
679	Characterization of hard DC-sputtered Si-based TiN coatings: the effect of composition and ion bombardment. <i>Surface and Coatings Technology</i> , <b>2004</b> , 188-189, 351-357	4.4	33
678	Hydrogen in InN: A ubiquitous phenomenon in molecular beam epitaxy grown material. <i>Applied Physics Letters</i> , <b>2010</b> , 96, 081907	3.4	32
677	Green, red and infrared Er-related emission in implanted GaN:Er and GaN:Er,O samples. <i>Journal of Applied Physics</i> , <b>2001</b> , 89, 6183-6188	2.5	32
676	Efficient temperature sensing using photoluminescence of Er/Yb implanted GaN thin films. <i>Sensors and Actuators B: Chemical</i> , <b>2017</b> , 248, 769-776	8.5	31
675	p-Type $\text{Cu}_x\text{O}$ Thin-Film Transistors Produced by Thermal Oxidation. <i>Journal of Display Technology</i> , <b>2013</b> , 9, 735-740		31
674	Properties of tantalum oxynitride thin films produced by magnetron sputtering: The influence of processing parameters. <i>Vacuum</i> , <b>2013</b> , 98, 63-69	3.7	31
673	The role of composition, morphology and crystalline structure in the electrochemical behaviour of $\text{TiN}_x$ thin films for dry electrode sensor materials. <i>Electrochimica Acta</i> , <b>2009</b> , 55, 59-67	6.7	31
672	Structural evolution of $\text{TiAlSiN}$ nanocomposite coatings. <i>Vacuum</i> , <b>2009</b> , 83, 1206-1212	3.7	31
671	Raman spectra and structural analysis in $\text{ZrO}_x\text{N}_y$ thin films. <i>Thin Solid Films</i> , <b>2006</b> , 515, 1132-1137	2.2	31
670	Mechanisms of Implantation Damage Formation in $\text{Al}_x\text{Ga}_{1-x}\text{N}$ Compounds. <i>Journal of Physical Chemistry C</i> , <b>2016</b> , 120, 7277-7283	3.8	30
669	Surface analysis of tiles and samples exposed to the first JET campaigns with the ITER-like wall. <i>Physica Scripta</i> , <b>2014</b> , T159, 014012	2.6	30
668	Nanocomposite Ag:TiN thin films for dry biopotential electrodes. <i>Applied Surface Science</i> , <b>2013</b> , 285, 40-48	6.7	30
667	Depth-resolved analysis of spontaneous phase separation in the growth of lattice-matched $\text{AlInN}$ . <i>Journal Physics D: Applied Physics</i> , <b>2010</b> , 43, 055406	3	30
666	Rapid thermal annealing of rare earth implanted ZnO epitaxial layers. <i>Optical Materials</i> , <b>2011</b> , 33, 1139-1142	3.4	30
665	OPTICAL DOPING OF NITRIDES BY ION IMPLANTATION. <i>Modern Physics Letters B</i> , <b>2001</b> , 15, 1281-1287	1.6	30
664	High In-content InGaN layers synthesized by plasma-assisted molecular-beam epitaxy: Growth conditions, strain relaxation, and In incorporation kinetics. <i>Journal of Applied Physics</i> , <b>2014</b> , 116, 233504	2.5	29
663	TiN <sub>x</sub> coated polycarbonate for bio-electrode applications. <i>Corrosion Science</i> , <b>2012</b> , 56, 49-57	6.8	29

662	Substrate effect on CdTe layers grown by metalorganic vapor phase epitaxy. <i>Applied Physics Letters</i> , <b>1997</b> , 70, 1314-1316	3-4	29
661	Tribocorrosion behaviour of ZrOxNy thin films for decorative applications. <i>Surface and Coatings Technology</i> , <b>2006</b> , 200, 6634-6639	4-4	29
660	Optical doping of ZnO with Tm by ion implantation. <i>Physica B: Condensed Matter</i> , <b>2003</b> , 340-342, 235-239	2.8	29
659	Comparison of low- and room-temperature damage formation in Ar ion implanted GaN and ZnO. <i>Nuclear Instruments &amp; Methods in Physics Research B</i> , <b>2013</b> , 307, 394-398	1.2	28
658	Luminescence of Eu ions in Al <sub>x</sub> Ga <sub>1-x</sub> N across the entire alloy composition range. <i>Physical Review B</i> , <b>2009</b> , 80,	3-3	28
657	Effect of annealing temperature on luminescence in Eu implanted GaN. <i>Optical Materials</i> , <b>2006</b> , 28, 780-784	3.4	28
656	Roughness in GaN/InGaN films and multilayers determined with Rutherford backscattering. <i>Nuclear Instruments &amp; Methods in Physics Research B</i> , <b>2004</b> , 217, 479-497	1.2	28
655	Ion beam analysis of fusion plasma-facing materials and components: facilities and research challenges. <i>Nuclear Fusion</i> , <b>2020</b> , 60, 025001	3-3	28
654	Utilization of native oxygen in Eu(RE)-doped GaN for enabling device compatibility in optoelectronic applications. <i>Scientific Reports</i> , <b>2016</b> , 6, 18808	4-9	28
653	TiAg <sub>x</sub> thin films for lower limb prosthesis pressure sensors: Effect of composition and structural changes on the electrical and thermal response of the films. <i>Applied Surface Science</i> , <b>2013</b> , 285, 10-18	6-7	27
652	Influence of the O/C ratio in the behaviour of TiC <sub>x</sub> O <sub>y</sub> thin films. <i>Surface and Coatings Technology</i> , <b>2007</b> , 201, 5587-5591	4-4	27
651	A design of selective solar absorber for high temperature applications. <i>Solar Energy</i> , <b>2018</b> , 172, 177-183	6.8	26
650	Electrochemical behaviour of nanocomposite Ag <sub>x</sub> :TiN thin films for dry biopotential electrodes. <i>Electrochimica Acta</i> , <b>2014</b> , 125, 48-57	6-7	26
649	First results and surface analysis strategy for plasma-facing components after JET operation with the ITER-like wall. <i>Physica Scripta</i> , <b>2014</b> , T159, 014016	2.6	26
648	Study of the relationship between crystal structure and luminescence in rare-earth-implanted Ga <sub>2</sub> O <sub>3</sub> nanowires during annealing treatments. <i>Journal of Materials Science</i> , <b>2014</b> , 49, 1279-1285	4-3	26
647	Visible and infrared luminescence study of Er doped Ga <sub>2</sub> O <sub>3</sub> and Er <sub>3</sub> Ga <sub>5</sub> O <sub>12</sub> . <i>Journal Physics D: Applied Physics</i> , <b>2008</b> , 41, 065406	3	26
646	Incorporation and stability of erbium in sapphire by ion implantation. <i>Nuclear Instruments &amp; Methods in Physics Research B</i> , <b>1995</b> , 106, 429-432	1.2	26
645	Direct observation of mono-vacancy and self-interstitial recovery in tungsten. <i>APL Materials</i> , <b>2019</b> , 7, 021103	5-7	25



644	Consolidation of W/Cu composites: Hot isostatic pressing and spark and pulse plasma sintering. <i>Fusion Engineering and Design</i> , <b>2015</b> , 98-99, 1950-1955	1.7	25
643	Single phase a-plane MgZnO epilayers for UV optoelectronics: substitutional behaviour of Mg at large contents. <i>CrystEngComm</i> , <b>2012</b> , 14, 1637-1640	3.3	25
642	Lattice site location of optical centers in GaN:Eu light emitting diode material grown by organometallic vapor phase epitaxy. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 111911	3.4	25
641	Indium kinetics during the plasma-assisted molecular beam epitaxy of semipolar (11 $\bar{2}$ ) InGaN layers. <i>Applied Physics Letters</i> , <b>2010</b> , 96, 181907	3.4	25
640	Tribological behaviour of Cl-implanted TiN coatings for biomedical applications. <i>Wear</i> , <b>2007</b> , 262, 1337-1345	3.5	25
639	Defect production in neutron irradiated GaN. <i>Nuclear Instruments &amp; Methods in Physics Research B</i> , <b>2006</b> , 249, 358-361	1.2	25
638	Up conversion from visible to ultraviolet in bulk ZnO implanted with Tm ions. <i>Applied Physics Letters</i> , <b>2005</b> , 87, 192108	3.4	25
637	Deuterium retention in tin (Sn) and lithium (Li) samples exposed to ISTTOK plasmas. <i>Nuclear Materials and Energy</i> , <b>2017</b> , 12, 709-713	2.1	24
636	Amorphisation of GaN during processing with rare earth ion beams. <i>Superlattices and Microstructures</i> , <b>2004</b> , 36, 737-745	2.8	24
635	Ion beam and photoluminescence studies of Er and O implanted GaN. <i>Nuclear Instruments &amp; Methods in Physics Research B</i> , <b>1999</b> , 147, 383-387	1.2	24
634	Assessment of erosion, deposition and fuel retention in the JET-ILW divertor from ion beam analysis data. <i>Nuclear Materials and Energy</i> , <b>2017</b> , 12, 559-563	2.1	23
633	Intense luminescence emission from rare-earth-doped MoO <sub>3</sub> nanoplates and lamellar crystals for optoelectronic applications. <i>Journal Physics D: Applied Physics</i> , <b>2014</b> , 47, 355105	3	23
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631	ZrOxNy decorative thin films prepared by the reactive gas pulsing process. <i>Journal Physics D: Applied Physics</i> , <b>2009</b> , 42, 195501	3	23
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489	CrAlSiN barrier layer to improve the thermal stability of W/CrAlSiN <sub>x</sub> /CrAlSiO <sub>y</sub> N <sub>x</sub> /SiAlO <sub>x</sub> solar thermal absorber. <i>Solar Energy Materials and Solar Cells</i> , <b>2019</b> , 191, 235-242	6.4	12
488	Corundum-to-spinel structural phase transformation in alumina. <i>Nuclear Instruments &amp; Methods in Physics Research B</i> , <b>2015</b> , 358, 136-141	1.2	11
487	Fuel inventory and material migration of JET main chamber plasma facing components compared over three operational periods. <i>Physica Scripta</i> , <b>2020</b> , T171, 014051	2.6	11
486	WC-Cu thermal barriers for fusion applications. <i>Surface and Coatings Technology</i> , <b>2018</b> , 355, 222-226	4.4	11
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479	Structural and optical properties of nitrogen doped ZnO films. <i>Vacuum</i> , <b>2009</b> , 83, 1274-1278	3.7	11
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477	Influence of Rapid Thermal Annealing on the Luminescence Properties of Nanoporous GaN Films. <i>Electrochemical and Solid-State Letters</i> , <b>2006</b> , 9, G150		11
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